

PF0141

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Product Preview

加急出货

MOS FET Power Amplifier Module for GSM Handy Phone

For GSM CLASS 4 890~915 MHz

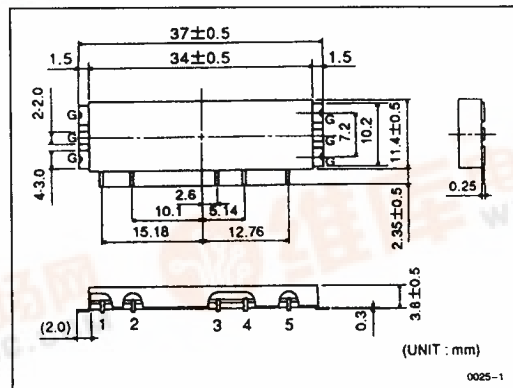
FEATURES

- High Efficiency45% typ.
- High Speed Switching0.9 μ s typ.
- Wide Power Control Range85 dB typ.

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Supply Voltage	V_{DD}	12	V
Supply Current	I_{DD}	3	A
APC Voltage	V_{APC}	4	V
Input Power	P_{in}	20	mW
Operating Case Temperature	T_C (op)	-30 ~ +100	$^\circ\text{C}$
Storage Temperature	T_{stg}	-30 ~ +100	$^\circ\text{C}$

OUTLINE DRAWING



PIN OUT

Pin No.	Pin Name
1	P_{in}/V_{APC}
2	V_{DD1}
3	V_{DD2}
4	V_{DD3}
5	P_{out}
G	GND

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$)

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain Cutoff Current	I_{DS}	—	—	100	μA	$V_{DD} = 12\text{V}, V_{APC} = 0\text{V}$
Total Efficiency	η_T	40	45	—	%	$P_{in} = 2\text{mW}, V_{DD} = 6\text{V}, P_{out} = 3.2\text{W}$ (at APC Controlled), $R_L = R_g = 50\Omega, T_C = 25^\circ\text{C}$
2nd Harmonic Distortion	2nd H.D.	—	-40	-30	dB	
3rd Harmonic Distortion	3rd H.D.	—	-40	-30	dB	
Input VSWR	VSWR (in)	—	2	3	—	
Output Power (1)	P_{out} (1)	3.6	4.5	—	W	$P_{in} = 2\text{mW}, V_{DD} = 6\text{V}, V_{APC} = 4\text{V}, R_L = R_g = 50\Omega, T_C = 25^\circ\text{C}$
Output Power (2)	P_{out} (2)	2.0	2.8	—	W	$P_{in} = 2\text{mW}, V_{DD} = 5.4\text{V}, V_{APC} = 4\text{V}, R_L = R_g = 50\Omega, T_C = 80^\circ\text{C}$
Isolation	—	—	-50	-40	dBm	$P_{in} = 2\text{mW}, V_{DD} = 6\text{V}, V_{APC} = 0.5\text{V}, R_L = R_g = 50\Omega, T_C = 25^\circ\text{C}$
Switching Time	t_R, t_F	—	0.9	2	μs	$P_{in} = 2\text{mW}, V_{DD} = 6\text{V}, P_{out} = 3.2\text{W}, R_L = R_g = 50\Omega, T_C = 25^\circ\text{C}$
Stability	—	—	No Parasitic Oscillation	—	—	$P_{in} = 2\text{mW}, V_{DD} = 7.5\text{V}, P_{out} \leq 3.2\text{W}$ (at APC Controlled), $R_g = 50\Omega, t = 20\text{sec}, T_C = 25^\circ\text{C}, \text{Output VSWR} = 20:1$ All Phases



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